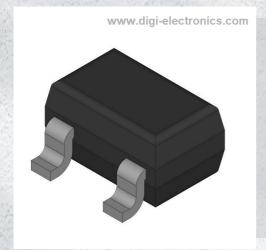


BC859CW135 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number BC859CW135-DG

Manufacturer NXP USA Inc.

Manufacturer Product Number BC859CW135

Description NOW NEXPERIA BC859CW - SMALL SIG

Detailed Description Bipolar (BJT) Transistor PNP 30 V 100 mA 100MHz 2

00 mW Surface Mount SOT-323



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

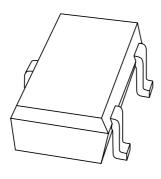
Manufacturer Product Number:	Manufacturer:
BC859CW135	NXP USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
30 V	650mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
15nA (ICBO)	420 @ 2mA, 5V
Power - Max:	Frequency - Transition:
200 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SOT-323

Environmental & Export classification

ECCN:	HTSUS:
EAR99	8541.21.0075

DISCRETE SEMICONDUCTORS

DATA SHEET



BC859W; BC860W PNP general purpose transistors

Product data sheet Supersedes data of 1997 Sep 03 1999 Apr 12



PNP general purpose transistors

BC859W; BC860W

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 45 V).

APPLICATIONS

• Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

PNP transistor in a SOT323 plastic package. NPN complements: BC849W and BC850W.

MARKING

TYPE NUMBER	MARKING CODE		
BC859W	4D*	BC860W	4H*
BC859BW	4B*	BC860BW	4F*
BC859CW	4C*	BC860CW	4G*

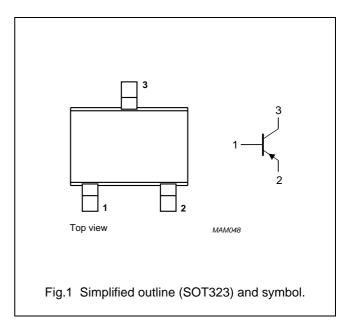
Note

1. * = -: Made in Hong Kong.

* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859W		_	-30	V
	BC860W		_	-50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859W		_	-30	V
	BC860W		_	-45	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC859W; BC860W

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	_	_	-15	nA
		I _E = 0; V _{CB} = -30 V; T _j = 150 °C	_	_	-4	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	-	_	-100	nA
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V};$				
	BC859W; BC860W	see Figs 2 and 3	220	_	800	
	BC859BW; BC860BW		220	_	475	
	BC859CW; BC860CW		420	_	800	
V _{CEsat}	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-300	mV
	voltage	$I_C = -100 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1	_	_	-650	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	600	_	750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	_	820	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	5	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{EB} = -500 \text{ mV}$; $f = 1 \text{ MHz}$	-	10	_	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	100	_	_	MHz
F	noise figure; BC859W; BC860W;	$\begin{split} I_C &= -200 \; \mu\text{A}; \; V_{CE} = -5 \; V; \; R_S = 2 \; k\Omega; \\ f &= 10 \; \text{Hz} \; \text{to} \; 15.7 \; \text{kHz} \end{split}$	_	_	4	dB
	BC859BW; BC860BW; BC859CW; BC860CW	I_C = -200 μA; V_{CE} = -5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	_	4	dB

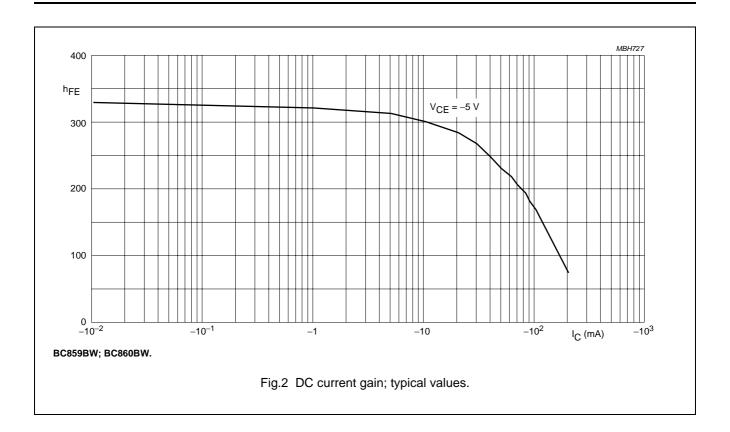
Note

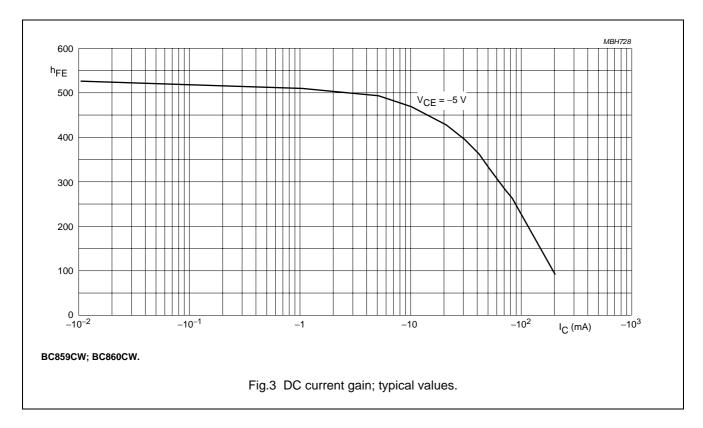
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

1999 Apr 12

PNP general purpose transistors

BC859W; BC860W





4

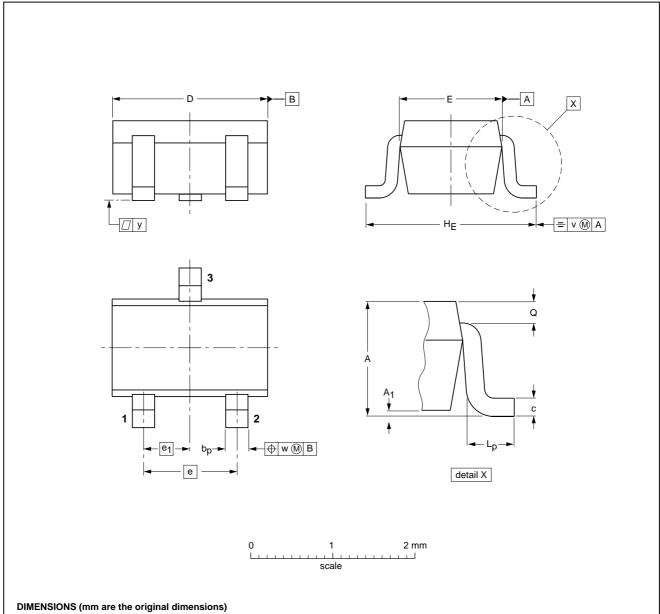
PNP general purpose transistors

BC859W; BC860W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS	(mm are	the	original	dimensions	.)

UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28

1999 Apr 12 5

PNP general purpose transistors

BC859W; BC860W

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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